

Digital transistors (built-in resistors)

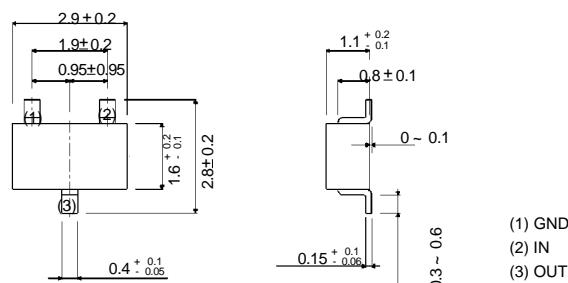
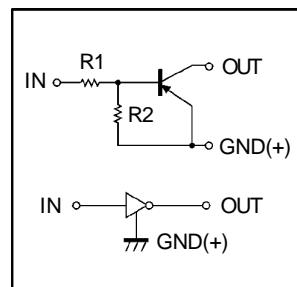
- Features**

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thinfilm resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.

- Structure**

PNP digital transistor (Built-in resistors type)

- Equivalent circuit**



EIAJ: SC—59

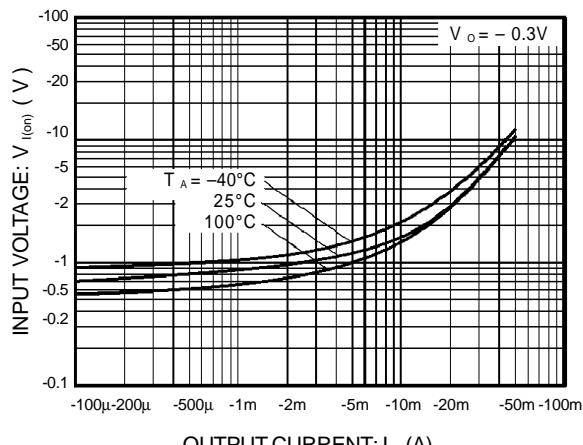
- Absolute maximum ratings($T_a=25^\circ\text{C}$)

Parameter	symbol	limits		unit
Supply voltage	V_{cc}	-50		V
Input voltage	V_{IN}	-40~+6		V
Output current	I_O	-70		mA
	$I_{O(\text{Max.})}$	-100		
Power dissipation	P_d	200		mW
Junction temperature	T_j	150		°C
Storage temperature	T_{stg}	-55~+150		°C

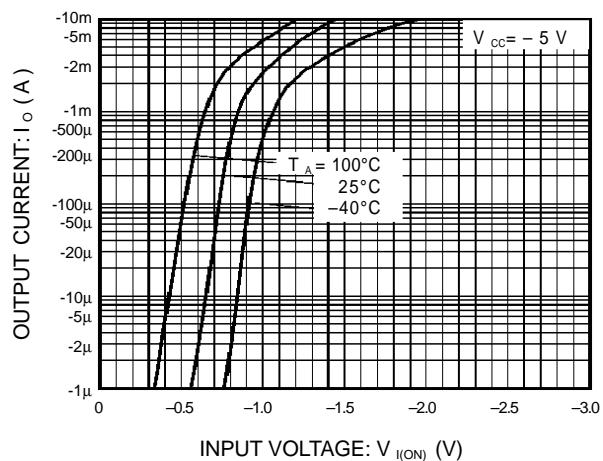
- Electrical characteristics($T_a=25^\circ\text{C}$)

Parameter	symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(\text{off})}$	—	—	-0.3	V	$V_{cc} = -5\text{V}, I_O = -100\mu\text{A}$
	$V_{I(\text{on})}$	-1.4	—	—		$V_O = -0.3\text{V}, I_O = -1\text{mA}$
Output Voltage	$V_{O(\text{on})}$	—	-0.1	-0.3	V	$I_O/I_I = -5\text{mA}/-0.25\text{mA}$
Input current	I_I	—	—	-0.88	mA	$V_I = -5\text{V}$
Output current	$I_{O(\text{off})}$	—	—	-0.5	μA	$V_{cc} = -50\text{V}, V_I = 0\text{V}$
DC current gain	G_I	68	—	—	—	$V_O = -5\text{V}, I_O = -5\text{mA}$
Input resistance	R_I	7	10	13	KΩ	—
Resistance ratio	R_2/R_1	3.7	4.7	5.7	—	—
Transition frequency	f_T	—	250	—	MHz	$V_{CE} = -10\text{V}, I_E = 5\text{mA}, f = 100\text{MHz}^*$

*Transition frequency of the device

ELECTRICAL CHARACTERISTIC CURVES


**Figure 1. Input voltage vs.output current
(ON characteristics)**



**Figure 2. Output current vs.input voltage
(OFF characteristics)**

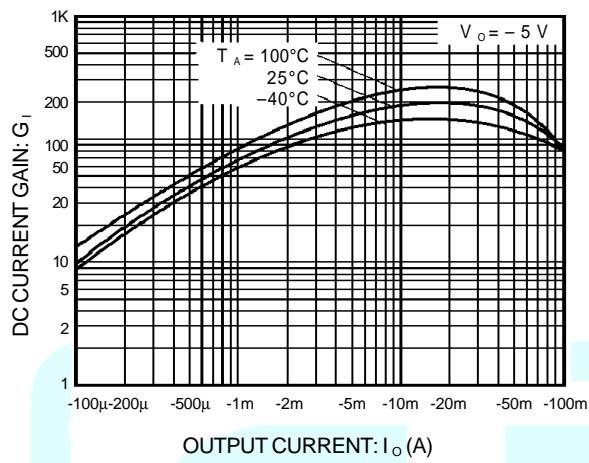


Figure 3. DC current gain vs.output current

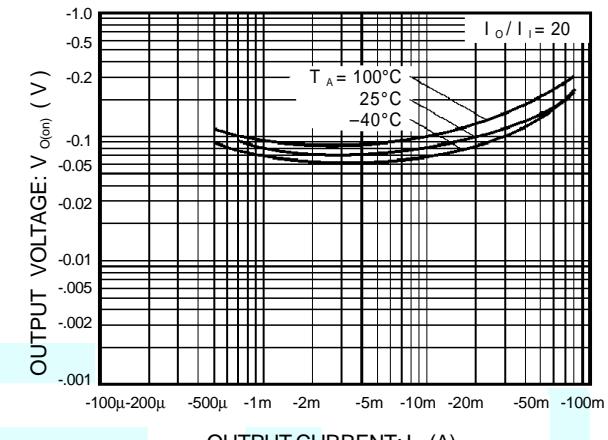


Figure 4. Output voltage vs.output current